

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EV2SC2714-X-S1
▶ Overseas	Part Number	2SC2714-X
▶ Equivalent	Part Number	2SC2714-X

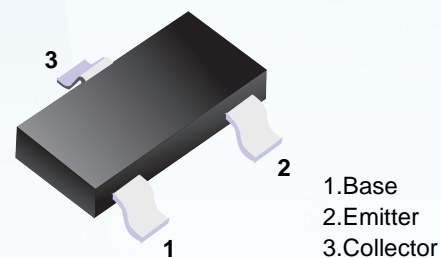
"S1" means SOT-23

EV is the abbreviation of name EVVO

■ NPN Transistors

■ Features

- Collector Current Capability $I_C=20\text{mA}$
- Collector Emitter Voltage $V_{CEO}=30\text{V}$



■ Simplified outline(SOT-23)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	40	V
Collector - Emitter Voltage	V_{CEO}	30	
Emitter - Base Voltage	V_{EBO}	4	
Collector Current - Continuous	I_C	20	mA
Collector Power Dissipation	P_C	100	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	1000	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	

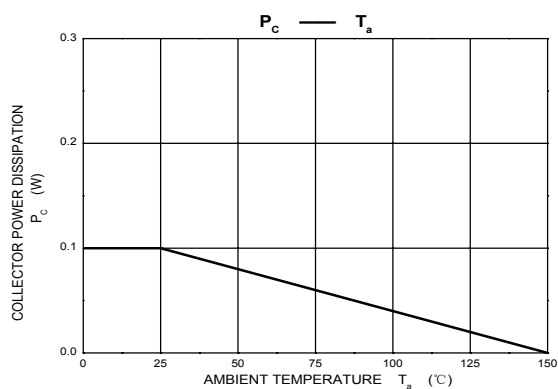
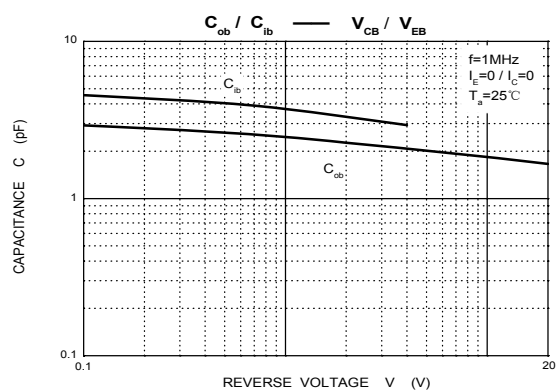
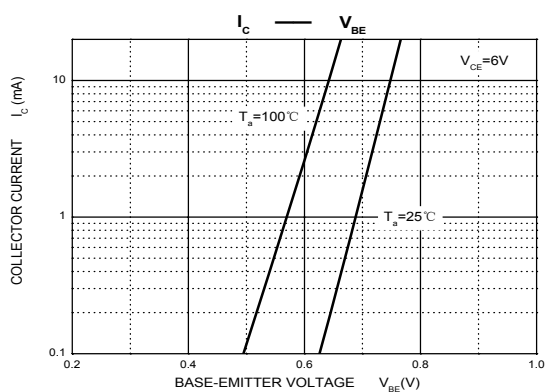
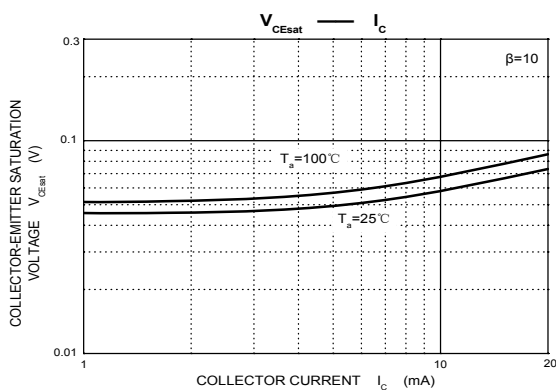
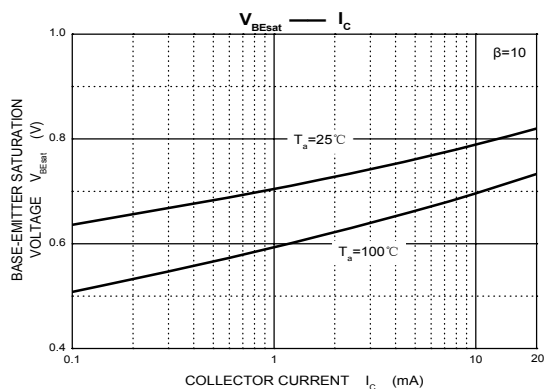
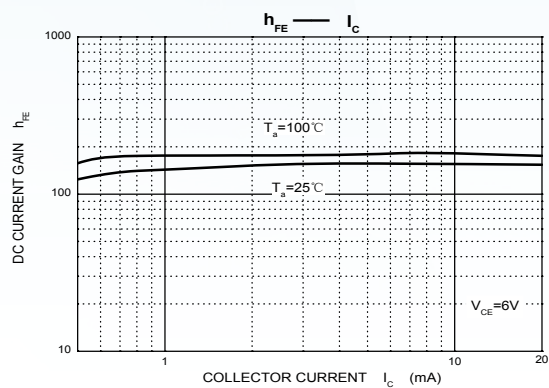
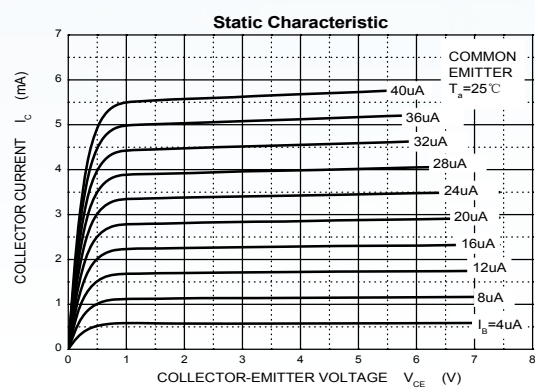
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100\ \mu\text{A}, I_E = 0$	40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1\ \text{mA}, I_B = 0$	30			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100\ \mu\text{A}, I_C = 0$	4			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 18\ \text{V}, I_E = 0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\ \text{V}, I_C = 0$			0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100\ \text{mA}, I_B = 10\ \text{mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100\ \text{mA}, I_B = 10\ \text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6\ \text{V}, I_C = 1\ \text{mA}$	40		200	
Noise Figure	NF	$V_{CE} = 6\ \text{V}, I_E = -1\ \text{mA}, f = 100\ \text{MHz}$		2.5	5	dB
Reverse Transfer capacitance	C_{re}	$V_{CB} = 6\ \text{V}, I_E = 0, f = 1\ \text{MHz}$		0.7		pF
Transition frequency	f_T	$V_{CE} = 6\ \text{V}, I_C = 1\ \text{mA}$		550		MHz

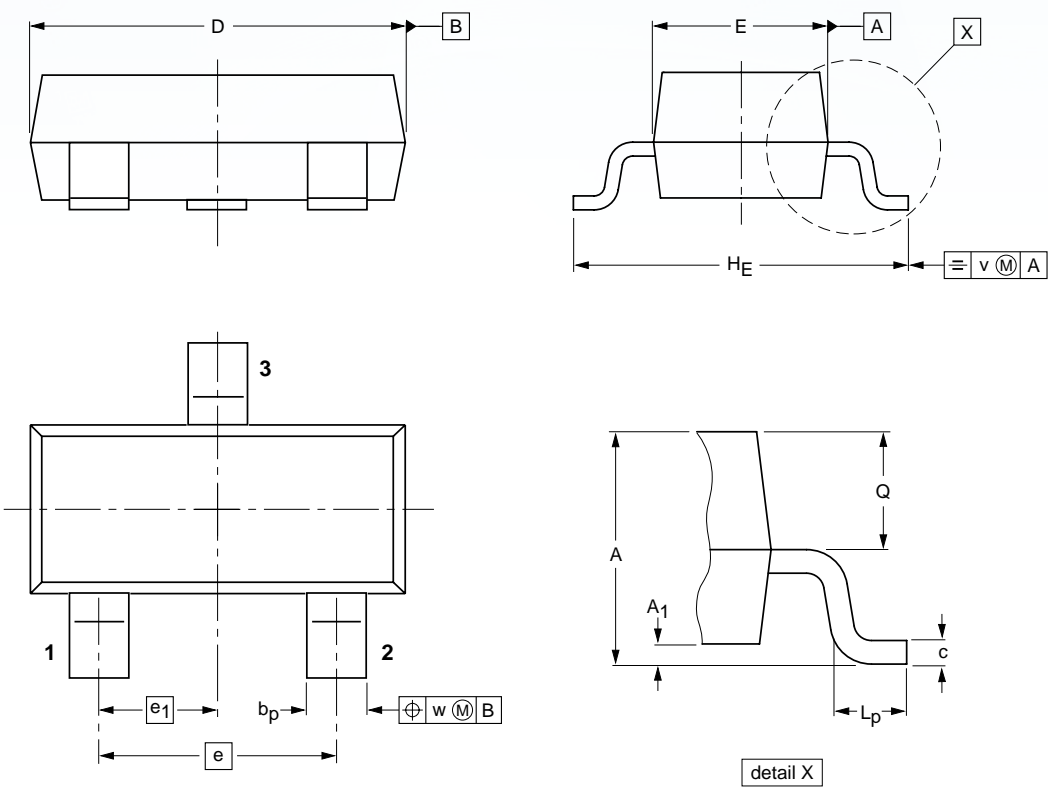
■ Classification of h_{FE}

Type	EV2SC2714-R-S1	EV2SC2714-O-S1	EV2SC2714-Y-S1
Range	40-80	70-140	100-200
Marking	QR	QO	QY

■ Typical Characteristics



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

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